

AMENDMENTS TO THE ABSTRACT

Please amend the Abstract as follows:

The present invention discloses a nonvolatile memory with spacer trapping structure, the nonvolatile memory comprising a semiconductor substrate. A gate oxide is formed on the semiconductor substrate. A gate structure is formed on the gate oxide. An isolation layer is formed over the sidewall of the gate structure. First spacers are formed on the sidewall of the isolation layer and becoming the spacer trapping structure for storing carrier. And the p-n junctions of source and drain regions are formed adjacent to the gate structure. Salicide is formed on the gate structure and the source and drain regions.